



DMN10H220LFVW

100V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	Rds(on) Max	Ι _D Tc = +25°C
100V	222mΩ @ VGs = 10V	11A
	$270m\Omega @ V_{GS} = 4.5V$	10A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Wettable Flank for Improved Optical Inspections
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please <u>contact us</u> or your local Diodes representative. <u>https://www.diodes.com/guality/product-definitions/</u>

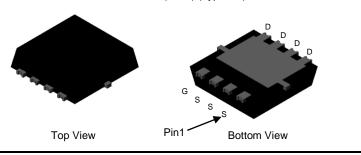
Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Load Switch

Mechanical Data

- Case: PowerDI[®]3333-8
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.072 grams (Approximate)



PowerDI3333-8 (SWP) (Type UX)

Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMN10H220LFVW-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMN10H220LFVW-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

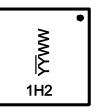
Notes:

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Haloger- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



 $\frac{1H2}{YY}WW = \text{Date Code Marking}$ $\frac{YY}{YY} = \text{Last Two Digits of Year (ex: 20 = 2020)}$ WW = Week Code (01 to 53)

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Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	100	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 6) VGs = 10V	lo	11 9	А	
Maximum Body Diode Forward Current (Note 6)	ls	11	А	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ідм	44	А	
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)	lsм	44	А	
Avalanche Current (Note 7)	L = 0.1mH	las	4.7	А
Avalanche Energy (Note 7)	L = 0.1mH	E _{AS}	1.1	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	PD	2.4	W
Thermal Resistance, Junction to Ambient (Note 5)		Reja	53	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	PD	41	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	3.02	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	100	—		V	$V_{GS} = 0V, I_D = 250 \mu A$
Zero Gate Voltage Drain Current	IDSS	_	_	1	μA	V _{DS} = 100V, V _{GS} = 0V
Gate-Source Leakage	lgss	_	_	100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 8)	· ·					
Gate Threshold Voltage	V _{GS(TH)}	1		2.5	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$
Static Drain-Source On-Resistance	Pro/otil	—	164	222	mΩ	$V_{GS} = 10V, I_{D} = 2A$
Static Drain-Source On-Resistance	Rds(on)	_	197	270	mΩ	V _{GS} = 4.5V, I _D = 1A
Diode Forward Voltage	Vsd	_	0.8	1.3	V	$V_{GS} = 0V$, $I_S = 2A$
DYNAMIC CHARACTERISTICS (Note 9)	· ·					
Input Capacitance	Ciss	—	366	—		
Output Capacitance	Coss	—	16	—	pF	$V_{DS} = 50V, f = 1MHz,$ $V_{GS} = 0V$
Reverse Transfer Capacitance	Crss	_	12	-		VGS = 0V
Gate Resistance	R _G	_	2.4	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	3.7	_		
Total Gate Charge (V _{GS} = 10V)	Qg	_	6.7	_	nC	Vpp = 50V. lp = 1.6A
Gate-Source Charge	Qgs	_	1.3	_		VDD = 50V, ID = 1.6A
Gate-Drain Charge	Q _{gd}	_	2.0	_		
Turn-On Delay Time	tD(ON)	_	6.2	_		
Turn-On Rise Time	tR	_	8.7	_		V _{DD} = 50V, V _{GS} = 4.5V,
Turn-Off Delay Time	t _{D(OFF)}	_	7.4	_	ns	R _G = 6.8Ω, I _D = 1.0A
Turn-Off Fall Time	tF	_	4.2	_	1	
Body Diode Reverse Recovery Time	trr	_	20	_	ns	
Body Diode Reverse Recovery Charge	Qrr	_	11	_	nC	−Is = 1.1A, dI/dt = 100A/µs

 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 Thermal resistance from junction to soldering point (on the exposed drain pad). Notes:

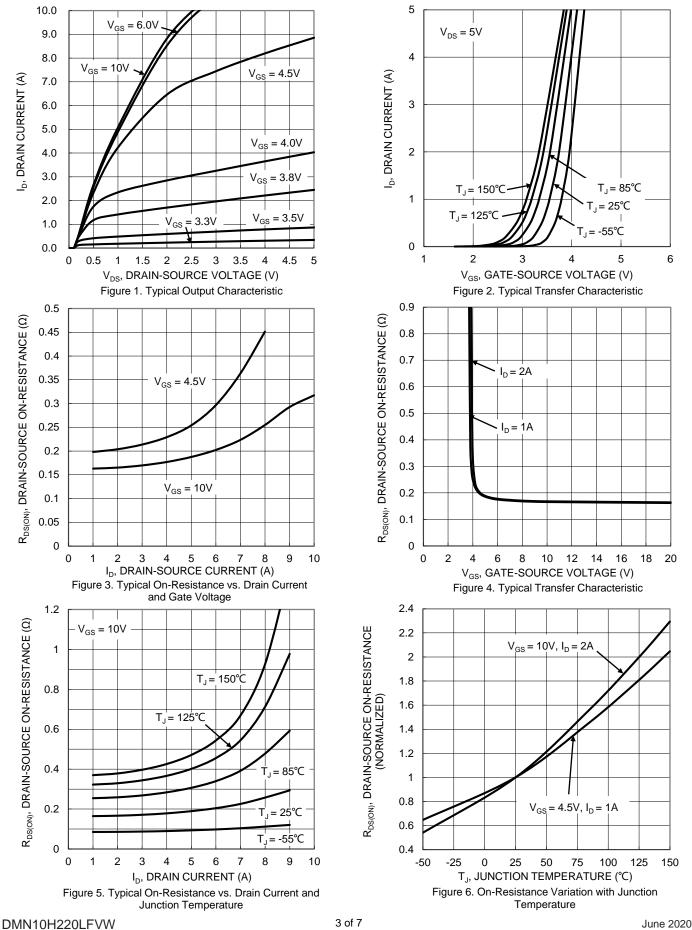
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.

8. Short duration pulse test used to minimize self-heating effect.

9. Guaranteed by design. Not subject to product testing.



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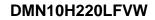


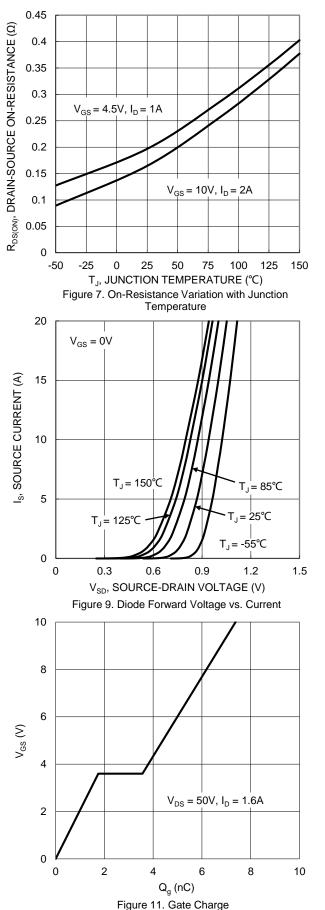
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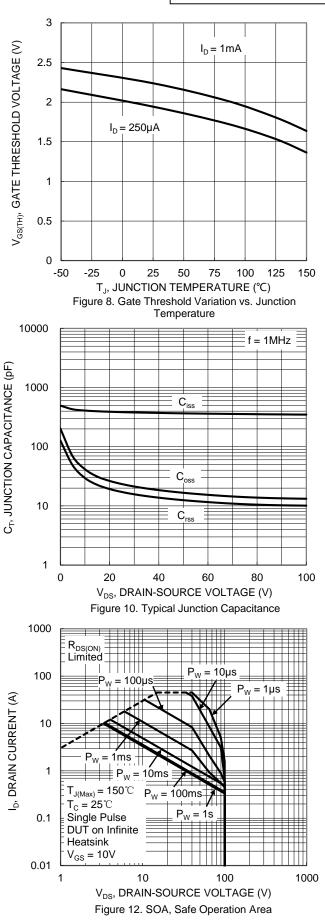
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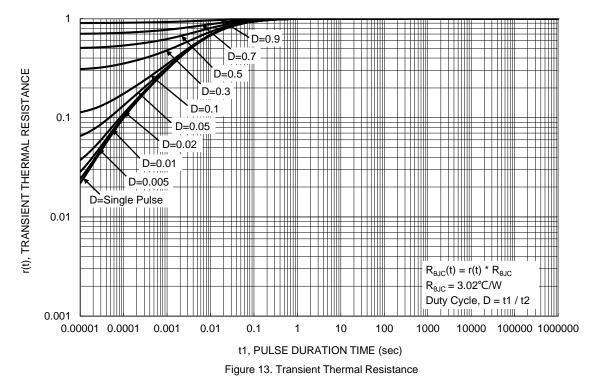






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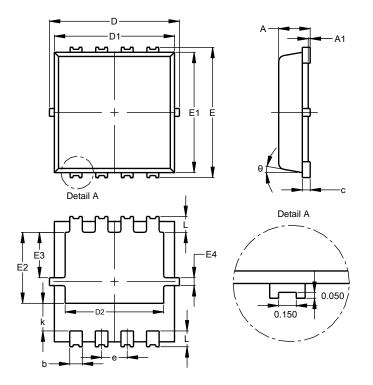




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

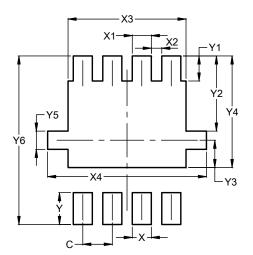


PowerDI3333-8 (SWP)					
(Type UX)					
Dim	Min	Min Max Ty			
Α	0.75	0.85	0.80		
A1	0.00	0.05			
Ь	0.25	0.40	0.32		
C	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
Е	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
e	_	_	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All I	All Dimensions in mm				

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
X3	2.600			
X4	3.500			
Y	0.700			
Y1	0.550			
Y2	1.650			
Y3	0.600			
Y4	2.450			
Y5	0.400			
Y6	3.700			



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